

## IN THE CLAIMS

Claims 1-12 (Canceled).

13 (Currently Amended). An integrated circuit comprising:  
a substrate;  
an integrated inductor formed over a first side of said substrate;  
an aperture formed in said substrate from a second side of said substrate  
underneath said inductor; and  
a dielectric material formed in said aperture such that the material directly  
underneath said inductor is entirely a dielectric material.

14 (Original). The circuit of claim 13 including an intervening layer between said inductor and said substrate.

15 (Original). The circuit of claim 14 wherein said intervening layer is a field oxide region.

16 (Original). The circuit of claim 14 wherein said aperture is formed completely through said substrate to said intervening layer.

17 (Original). The circuit of claim 16 wherein said aperture encompasses the entire region beneath said integrated inductor.

18 (Original). An integrated circuit comprising:  
a substrate;  
an inductor formed over a first side of said substrate;  
an aperture formed in said substrate from a second side of said substrate  
underneath said inductor and extending completely through said substrate from said second side  
a dielectric material filling said aperture  
a dielectric material also coating the back side of said substrate; and  
an intervening layer between said inductor and said substrate.

19 (Original). The circuit of claim 18 wherein said intervening layer is a field oxide region.

20 (Original). The circuit of claim 19 wherein said aperture encompasses the entire region beneath said integrated inductor.

Claim 21 (Canceled).

22 (New). An integrated circuit comprising:  
a semiconductor substrate;  
a dielectric layer over said substrate;  
an inductor formed over a first side of said substrate over said dielectric layer;  
an aperture in said substrate directly underneath said inductor and extending completely through said substrate from said second side of said substrate to said first side of said substrate; and  
a dielectric filling said aperture such that the material beneath said inductor is all dielectric material.

23 (New). The circuit of claim 22 wherein said inductor is an integrated inductor.

24 (New). The circuit of claim 23 wherein said dielectric layer includes a field oxide region.

25 (New). The circuit of claim 23 wherein said aperture is formed completely through said substrate to said dielectric layer.

26 (New). The circuit of claim 25 wherein said aperture encompasses the entire region beneath said inductor.